

TOSHIBA FIELD EFFECT TRANSISTOR SILICON P CHANNEL MOS TYPE

2SJ440

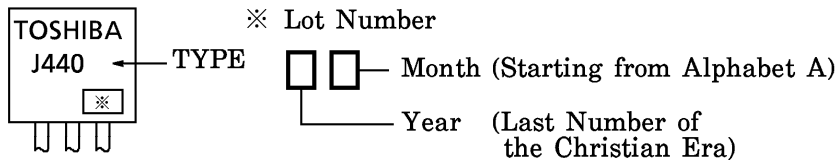
AUDIO FREQUENCY POWER AMPLIFIER APPLICATION

- High Breakdown Voltage : $V_{DSS} = -180\text{ V}$
- High Forward Transfer Admittance : $|Y_{fs}| = 4.0\text{ S (Typ.)}$

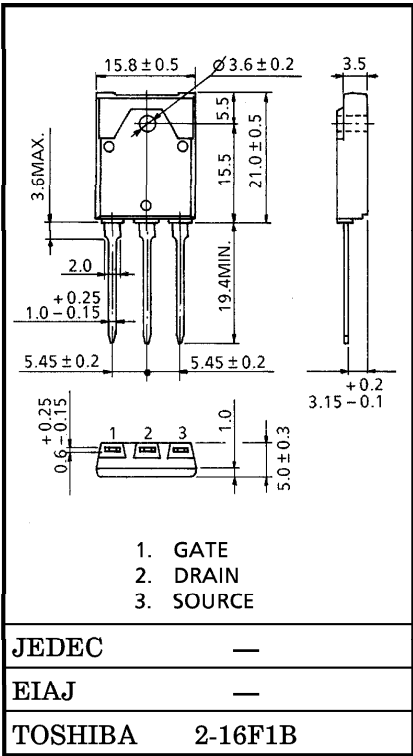
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	-180	V
Gate-Source Voltage	V_{GSS}	±20	V
Drain Current	I_D	-9	A
Power Dissipation (Tc = 25°C)	P_D	80	W
Channel Temperature	T_{ch}	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

MARKING



Unit in mm



Weight : 5.8 g (Typ.)

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	I_{GSS}	$V_{DS} = 0, V_{GS} = \pm 20 \text{ V}$	—	—	± 0.5	μA
Drain-Source Breakdown Voltage	$V_{(BR) DSS}$	$I_D = -10 \text{ mA}, V_{GS} = 0$	-180	—	—	V
Gate-Source Cut-off Current	$V_{GS (OFF)}$ (Note)	$V_{DS} = -10 \text{ V}, I_D = -0.1 \text{ A}$	-1.4	—	-2.8	V
Drain-Source Saturation Voltage	$V_{DS (ON)}$	$I_D = -6 \text{ A}, V_{GS} = -10 \text{ V}$	—	-1.5	-5.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10 \text{ V}, I_D = -3 \text{ A}$	—	4.0	—	S
Input Capacitance	C_{iss}	$V_{DS} = -30 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	—	1300	—	pF
Output Capacitance	C_{oss}	$V_{DS} = -30 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	—	350	—	pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = -30 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	—	200	—	pF

(Note) : $V_{GS (OFF)}$ Classification Y : -1.4 ~ -2.8

This transistor is the electrostatic sensitive device.
Please handle with caution.